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## What is "[Embedded - Microcontrollers](#)"?

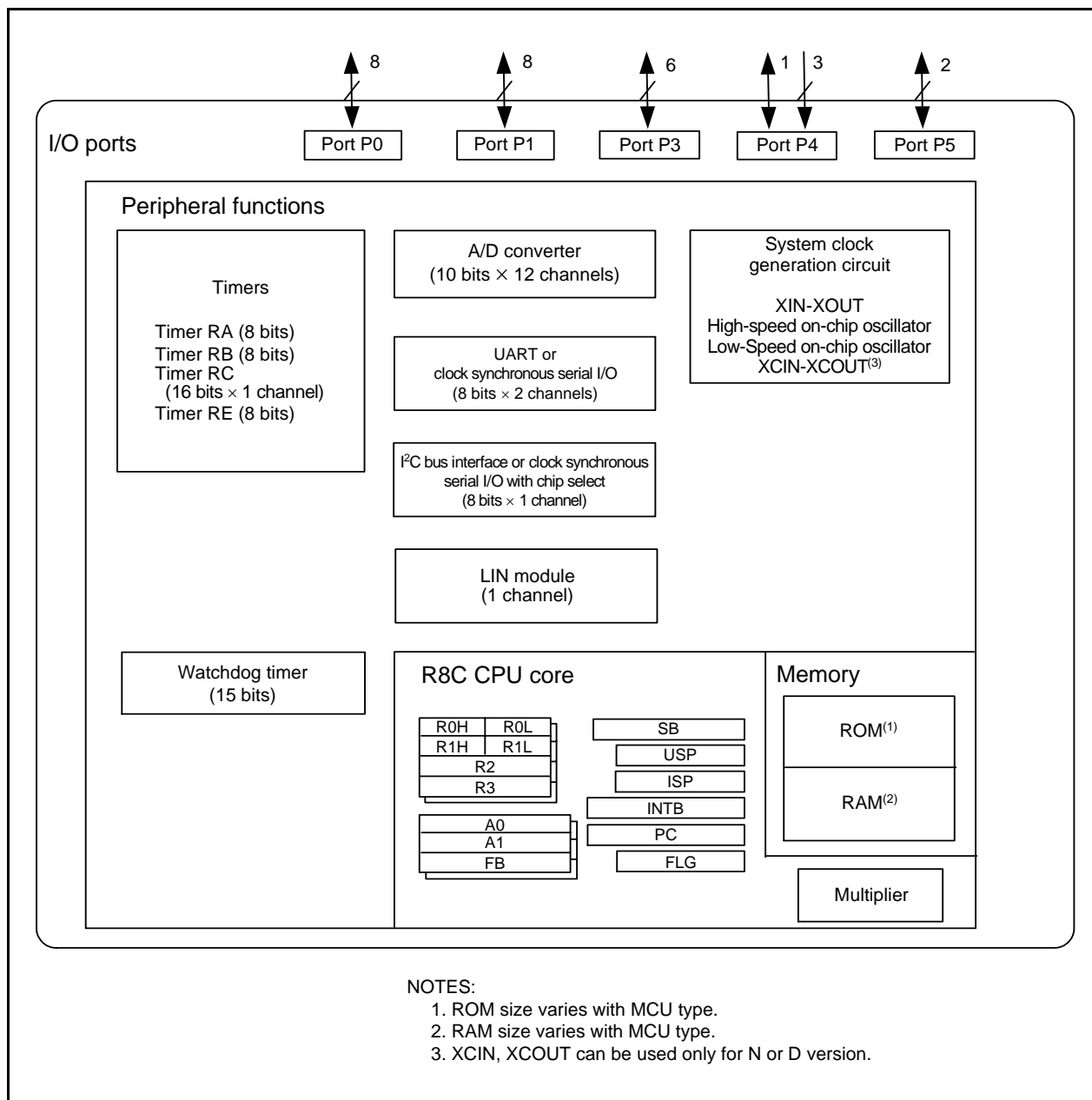
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

## Applications of "[Embedded - Microcontrollers](#)"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I <sup>2</sup> C, LINbus, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	24KB (24K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1.5K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21275syfp-x6">https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21275syfp-x6</a>

### 1.3 Block Diagram

Figure 1.1 shows a Block Diagram.



**Figure 1.1 Block Diagram**

## 1.4 Product Information

Table 1.3 lists the Product Information for R8C/26 Group and Table 1.4 lists the Product Information for R8C/27 Group.

**Table 1.3 Product Information for R8C/26 Group**

**Current of Sep. 2008**

Part No.	ROM Capacity	RAM Capacity	Package Type	Remarks		
R5F21262SNFP	8 Kbytes	512 bytes	PLQP0032GB-A	N version		
R5F21264SNFP	16 Kbytes	1 Kbyte	PLQP0032GB-A			
R5F21265SNFP	24 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21266SNFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21262SDFP	8 Kbytes	512 bytes	PLQP0032GB-A	D version		
R5F21264SDFP	16 Kbytes	1 Kbyte	PLQP0032GB-A			
R5F21265SDFP	24 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21266SDFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21264JFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	J version		
R5F21266JFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21264KFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	K version		
R5F21266KFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21262SNXXXFP	8 Kbytes	512 bytes	PLQP0032GB-A	N version	Factory programming product <sup>(1)</sup>	
R5F21264SNXXXFP	16 Kbytes	1 Kbyte	PLQP0032GB-A			
R5F21265SNXXXFP	24 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21266SNXXXFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21262SDXXXFP	8 Kbytes	512 bytes	PLQP0032GB-A	D version		
R5F21264SDXXXFP	16 Kbytes	1 Kbyte	PLQP0032GB-A			
R5F21265SDXXXFP	24 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21266SDXXXFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21264JXXXFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	J version		
R5F21266JXXXFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A			
R5F21264KXXXFP	16 Kbytes	1 Kbyte	PLQP0032GB-A	K version		
R5F21266KXXXFP	32 Kbytes	1.5 Kbytes	PLQP0032GB-A			

NOTE:

1. The user ROM is programmed before shipment.

## 1.6 Pin Functions

Table 1.5 lists Pin Functions.

**Table 1.5 Pin Functions**

Type	Symbol	I/O Type	Description
Power supply input	VCC, VSS	I	Apply 2.2 to 5.5 V (J, K version are 2.7 to 5.5 V) to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	I	Power supply for the A/D converter. Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input "L" on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XIN clock input	XIN	I	These pins are provided for XIN clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins. To use an external clock, input it to the XIN pin and leave the XOUT pin open.
XIN clock output	XOUT	O	
XCIN clock input (N, D version)	XCIN	I	These pins are provided for XCIN clock generation circuit I/O. Connect a crystal oscillator between the XCIN and XCOUNT pins. To use an external clock, input it to the XCIN pin and leave the XCOUNT pin open.
XCIN clock output (N, D version)	XCOUT	O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}, \overline{\text{INT1}}, \overline{\text{INT3}}$	I	$\overline{\text{INT}}$ interrupt input pins
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer RA	TRA0	O	Timer RA output pin
	TRAIO	I/O	Timer RA I/O pin
Timer RB	TRBO	O	Timer RB output pin
Timer RC	TRCLK	I	External clock input pin
	TRCTR	I	External trigger input pin
	TRCIOA, TRCIOB, TRCIO, TRCIOD	I/O	Sharing output-compare output / input-capture input / PWM / PWM2 output pins
Timer RE	TREO	O	Timer RE output pin
Serial interface	CLK0, CLK1	I/O	Clock I/O pin
	RXD0, RXD1	I	Receive data input pin
	TXD0, TXD1	O	Transmit data output pin
I <sup>2</sup> C bus interface	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
Clock synchronous serial I/O with chip select	SSI	I/O	Data I/O pin
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin
	SSCK	I/O	Clock I/O pin
	SSO	I/O	Data I/O pin
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter
A/D converter	AN0 to AN11	I	Analog input pins to A/D converter
I/O port	P0_0 to P0_7, P1_0 to P1_7, P3_1, P3_3 to P3_7, P4_5, P5_3, P5_4	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P1_0 to P1_7 also function as LED drive ports (N, D version).
Input port	P4_2, P4_6, P4_7	I	Input-only ports

I: Input      O: Output      I/O: Input and output

### 3.2 R8C/27 Group

Figure 3.2 is a Memory Map of R8C/27 Group. The R8C/27 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

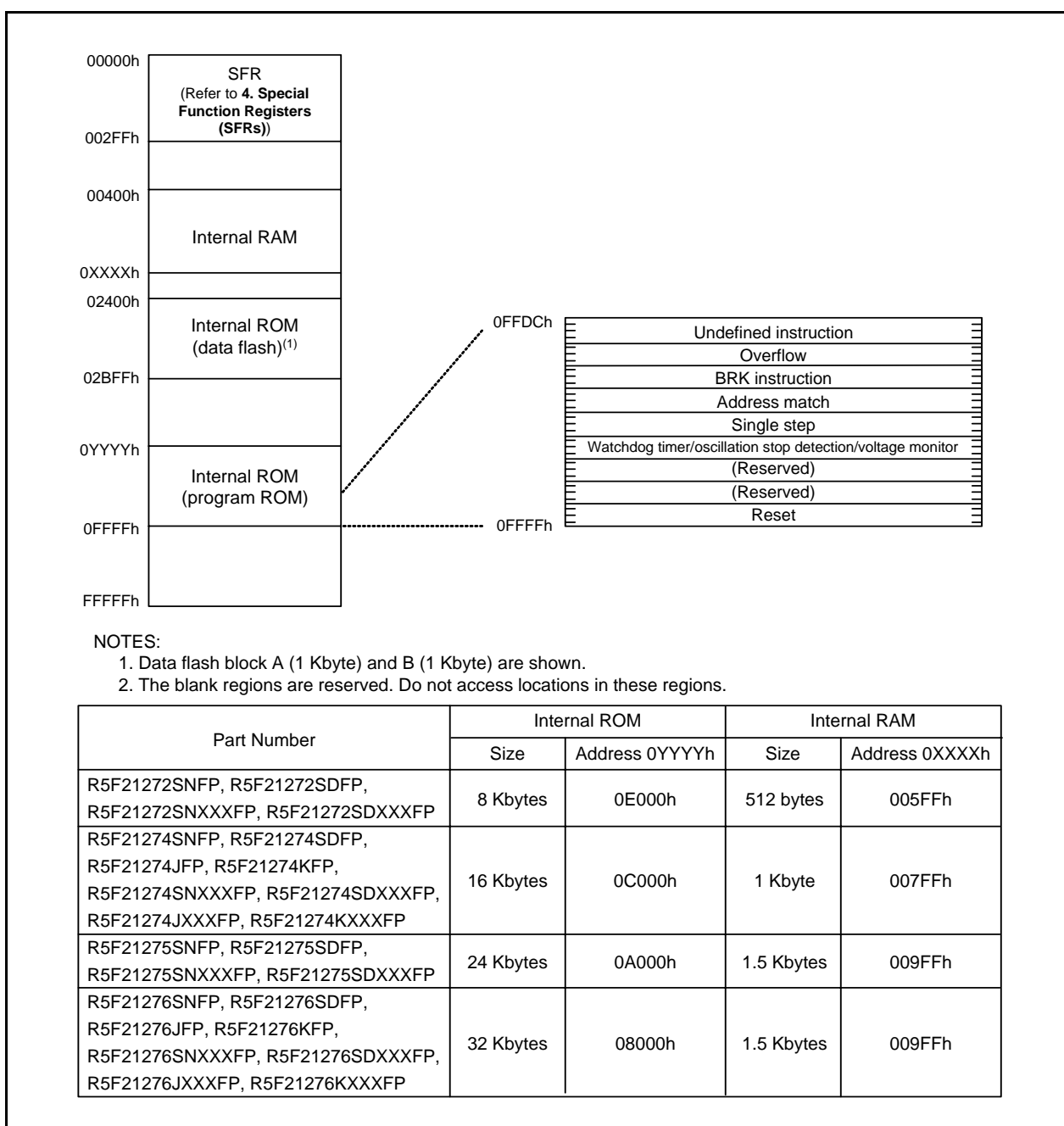
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.

The internal RAM area is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



**Figure 3.2 Memory Map of R8C/27 Group**

**Table 4.2 SFR Information (2)(1)**

Address	Register	Symbol	After reset
0030h			
0031h	Voltage Detection Register 1 (2)	VCA1	00001000b
0032h	Voltage Detection Register 2 (2)	VCA2	<ul style="list-style-type: none"> <li>• N, D version 00h(3)</li> <li>00100000b(4)</li> <li>• J, K version 00h(7)</li> <li>01000000b(8)</li> </ul>
0033h			
0034h			
0035h			
0036h	Voltage Monitor 1 Circuit Control Register (5)	VW1C	<ul style="list-style-type: none"> <li>• N, D version 00001000b</li> <li>• J, K version 0000X000b(7)</li> <li>0100X001b(8)</li> </ul>
0037h	Voltage Monitor 2 Circuit Control Register (5)	VW2C	00h
0038h	Voltage Monitor 0 Circuit Control Register (6)	VW0C	0000X000b(3)
0039h			0100X001b(4)
003Fh			
0040h			
0041h			
0042h			
0043h			
0044h			
0045h			
0046h			
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h			
0049h			
004Ah	Timer RE Interrupt Control Register	TREIC	XXXXX000b
004Bh			
004Ch			
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU/IIC bus Interrupt Control Register(9)	SSUIC/IICIC	XXXXX000b
0050h			
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h			
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh			
005Ch			
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh			
005Fh			
0060h			
006Fh			
0070h			
007Fh			

X: Undefined

**NOTES:**

- The blank regions are reserved. Do not access locations in these regions.
- (N, D version) Software reset, watchdog timer reset, voltage monitor 1 reset, or voltage monitor 2 reset do not affect this register.  
(J, K version) Software reset, watchdog timer reset, or voltage monitor 2 reset do not affect this register.
- The LVD0ON bit in the OFS register is set to 1 and hardware reset.
- Power-on reset, voltage monitor 0 reset or the LVD0ON bit in the OFS register is set to 0, and hardware reset.
- (N, D version) Software reset, watchdog timer reset, voltage monitor 1 reset, or voltage monitor 2 reset do not affect b2 and b3.  
(J, K version) Software reset, watchdog timer reset, or voltage monitor 2 reset do not affect b2 and b3.
- (N, D version) Software reset, watchdog timer reset, voltage monitor 1 reset, or voltage monitor 2 reset do not affect this register.  
(J, K version) These regions are reserved. Do not access locations in these regions.
- The LVD1ON bit in the OFS register is set to 1 and hardware reset.
- Power-on reset, voltage monitor 1 reset, or the LVD1ON bit in the OFS register is set to 0 and hardware reset.
- Selected by the IICSEL bit in the PMR register.

**Table 4.7 SFR Information (7)(1)**

Address	Register	Symbol	After reset
0180h			
0181h			
0182h			
0183h			
0184h			
0185h			
0186h			
0187h			
0188h			
0189h			
018Ah			
018Bh			
018Ch			
018Dh			
018Eh			
018Fh			
0190h			
0191h			
0192h			
0193h			
0194h			
0195h			
0196h			
0197h			
0198h			
0199h			
019Ah			
019Bh			
019Ch			
019Dh			
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h			
01B3h	Flash Memory Control Register 4	FMR4	01000000b
01B4h			
01B5h	Flash Memory Control Register 1	FMR1	1000000Xb
01B6h			
01B7h	Flash Memory Control Register 0	FMR0	00000001b
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			
FFFFh	Option Function Select Register	OFS	(Note 2)

X: Undefined

## NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. The OFS register cannot be changed by a program. Use a flash programmer to write to it.

**Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO40M	High-speed on-chip oscillator frequency temperature • supply voltage dependence	VCC = 4.75 to 5.25 V 0°C ≤ Topr ≤ 60°C <sup>(2)</sup>	39.2	40	40.8	MHz
		VCC = 3.0 to 5.5 V -20°C ≤ Topr ≤ 85°C <sup>(2)</sup>	38.8	40	41.2	MHz
		VCC = 3.0 to 5.5 V -40°C ≤ Topr ≤ 85°C <sup>(2)</sup>	38.4	40	41.6	MHz
		VCC = 2.7 to 5.5 V -20°C ≤ Topr ≤ 85°C <sup>(2)</sup>	38	40	42	MHz
		VCC = 2.7 to 5.5 V -40°C ≤ Topr ≤ 85°C <sup>(2)</sup>	37.6	40	42.4	MHz
		VCC = 2.2 to 5.5 V -20°C ≤ Topr ≤ 85°C <sup>(3)</sup>	35.2	40	44.8	MHz
		VCC = 2.2 to 5.5 V -40°C ≤ Topr ≤ 85°C <sup>(3)</sup>	34	40	46	MHz
		VCC = 5.0 V ± 10% -20°C ≤ Topr ≤ 85°C <sup>(2)</sup>	38.8	40	40.8	MHz
		VCC = 5.0 V ± 10% -40°C ≤ Topr ≤ 85°C <sup>(2)</sup>	38.4	40	40.8	MHz
	High-speed on-chip oscillator frequency when correction value in FRA7 register is written to FRA1 register <sup>(4)</sup>	VCC = 5.0 V, Topr = 25°C	—	36.864	—	MHz
		VCC = 3.0 to 5.5 V -20°C ≤ Topr ≤ 85°C	-3%	—	3%	%
—	Value in FRA1 register after reset		08h <sup>(3)</sup>	—	F7h <sup>(3)</sup>	—
—	Oscillation frequency adjustment unit of high-speed on-chip oscillator	Adjust FRA1 register (value after reset) to -1	—	+0.3	—	MHz
—	Oscillation stability time		—	10	100	μs
—	Self power consumption at oscillation	VCC = 5.0 V, Topr = 25°C	—	400	—	μA

## NOTES:

1. VCC = 2.2 to 5.5 V, Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. These standard values show when the FRA1 register value after reset is assumed.
3. These standard values show when the corrected value of the FRA6 register is written to the FRA1 register.
4. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

**Table 5.11 Low-speed On-Chip Oscillator Circuit Electrical Characteristics**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		30	125	250	kHz
—	Oscillation stability time		—	10	100	μs
—	Self power consumption at oscillation	VCC = 5.0 V, Topr = 25°C	—	15	—	μA

## NOTE:

1. VCC = 2.2 to 5.5 V, Topr = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.

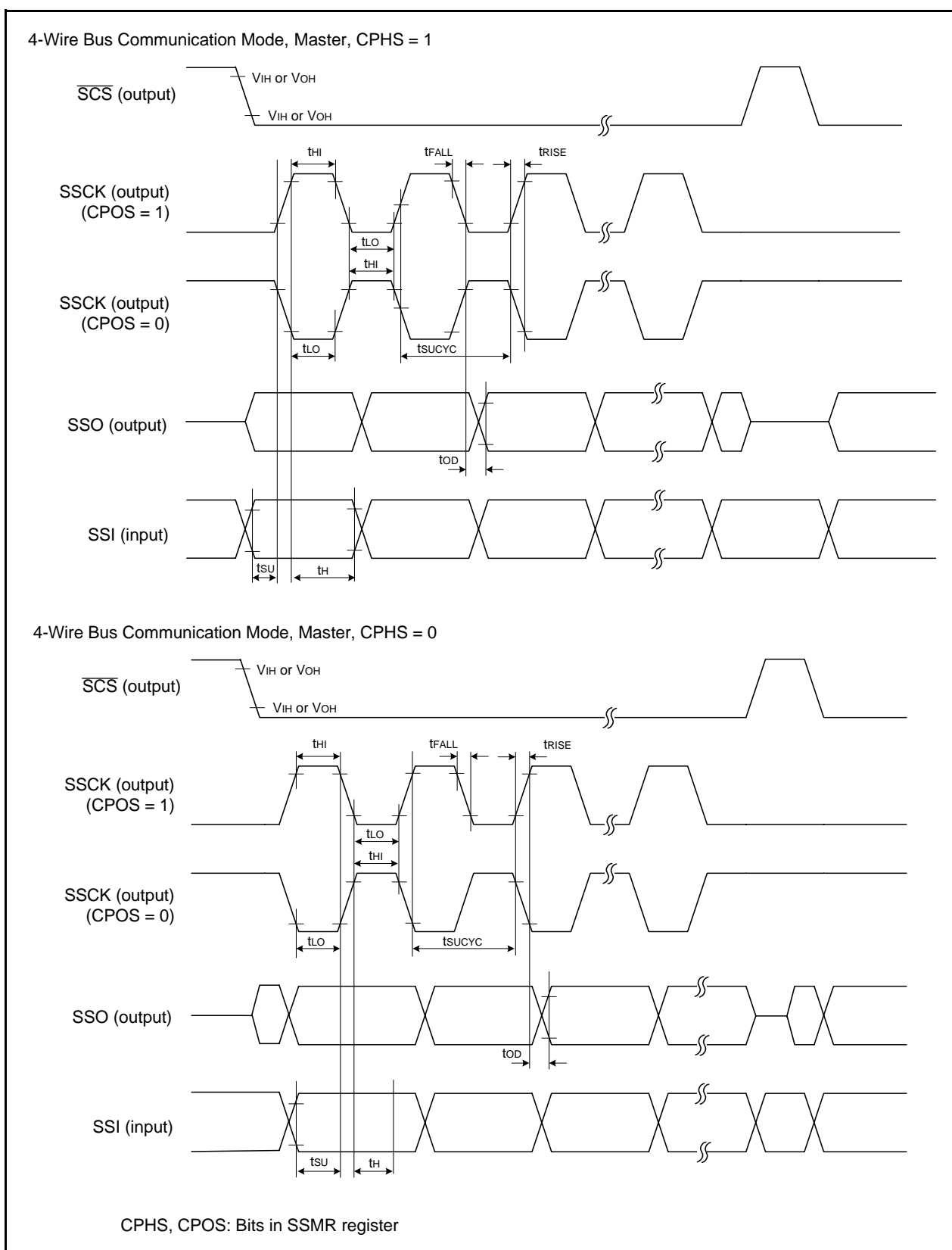
**Table 5.12 Power Supply Circuit Timing Characteristics**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
td(P-R)	Time for internal power supply stabilization during power-on <sup>(2)</sup>		1	—	2000	μs
td(R-S)	STOP exit time <sup>(3)</sup>		—	—	150	μs

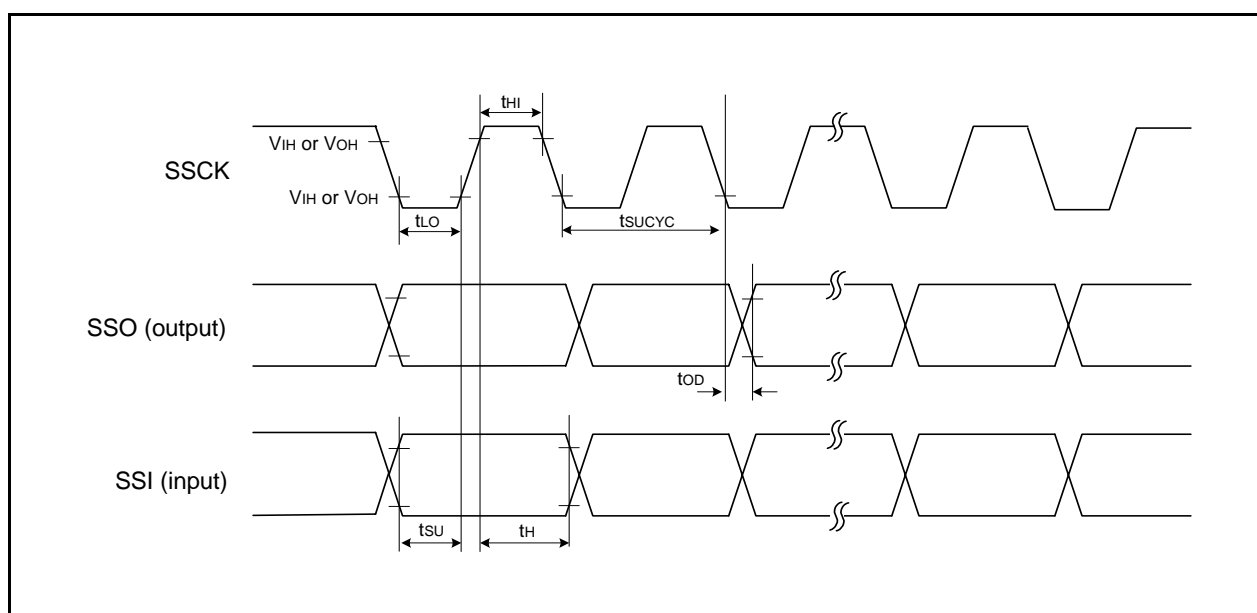
## NOTES:

1. The measurement condition is VCC = 2.2 to 5.5 V and Topr = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until system clock supply starts after the interrupt is acknowledged to exit stop mode.





**Figure 5.4 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)**



**Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)**

**Table 5.22 Electrical Characteristics (3) [V<sub>CC</sub> = 3 V]**

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V <sub>OH</sub>	Output "H" voltage	Except P1_0 to P1_7, XOUT	I <sub>OH</sub> = -1 mA		V <sub>CC</sub> - 0.5	—	V <sub>CC</sub>	V
		P1_0 to P1_7	Drive capacity HIGH	I <sub>OH</sub> = -5 mA	V <sub>CC</sub> - 0.5	—	V <sub>CC</sub>	V
			Drive capacity LOW	I <sub>OH</sub> = -1 mA	V <sub>CC</sub> - 0.5	—	V <sub>CC</sub>	V
		XOUT	Drive capacity HIGH	I <sub>OH</sub> = -0.1 mA	V <sub>CC</sub> - 0.5	—	V <sub>CC</sub>	V
			Drive capacity LOW	I <sub>OH</sub> = -50 μA	V <sub>CC</sub> - 0.5	—	V <sub>CC</sub>	V
V <sub>OL</sub>	Output "L" voltage	Except P1_0 to P1_7, XOUT	I <sub>OL</sub> = 1 mA		—	—	0.5	V
		P1_0 to P1_7	Drive capacity HIGH	I <sub>OL</sub> = 5 mA	—	—	0.5	V
			Drive capacity LOW	I <sub>OL</sub> = 1 mA	—	—	0.5	V
		XOUT	Drive capacity HIGH	I <sub>OL</sub> = 0.1 mA	—	—	0.5	V
			Drive capacity LOW	I <sub>OL</sub> = 50 μA	—	—	0.5	V
V <sub>T+</sub> -V <sub>T-</sub>	Hysteresis	INT0, INT1, INT3, KI0, KI1, KI2, KI3, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.3	—	V
		RESET			0.1	0.4	—	V
I <sub>IH</sub>	Input "H" current		V <sub>I</sub> = 3 V, V <sub>CC</sub> = 3 V		—	—	4.0	μA
I <sub>IL</sub>	Input "L" current		V <sub>I</sub> = 0 V, V <sub>CC</sub> = 3 V		—	—	-4.0	μA
R <sub>PULLUP</sub>	Pull-up resistance		V <sub>I</sub> = 0 V, V <sub>CC</sub> = 3 V		66	160	500	kΩ
R <sub>FXIN</sub>	Feedback resistance	XIN			—	3.0	—	MΩ
R <sub>FXCIN</sub>	Feedback resistance	XCIN			—	18	—	MΩ
V <sub>RAM</sub>	RAM hold voltage		During stop mode		1.8	—	—	V

**NOTE:**

- V<sub>CC</sub> = 2.7 to 3.3 V at T<sub>opr</sub> = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

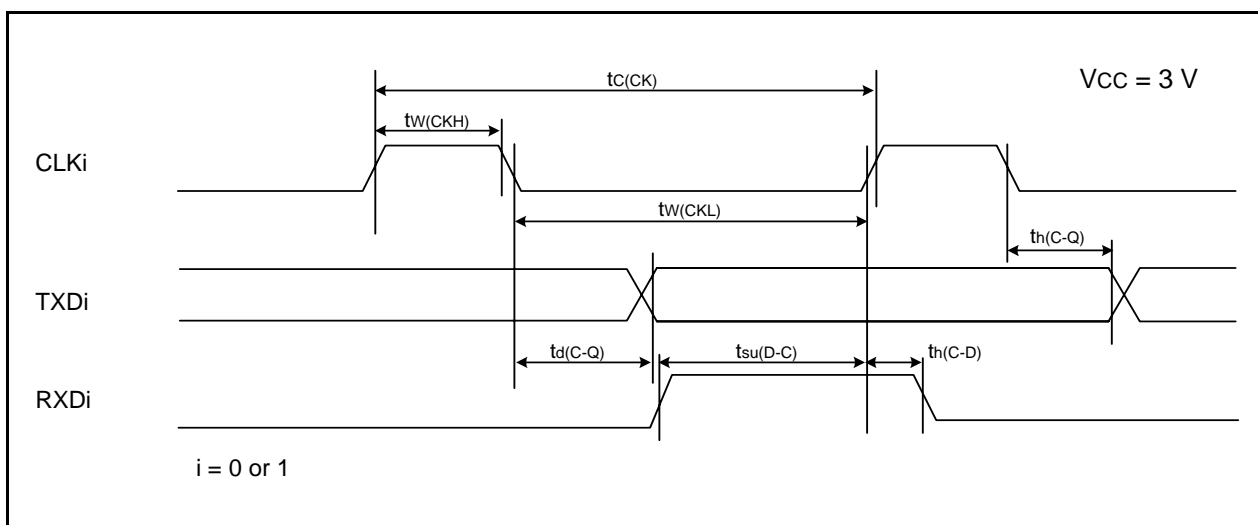
**Table 5.23 Electrical Characteristics (4) [V<sub>CC</sub> = 3 V]**  
**(T<sub>opr</sub> = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)**

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
I <sub>CC</sub>	Power supply current (V <sub>CC</sub> = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are V <sub>SS</sub>	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on f <sub>OCO</sub> = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN clock off High-speed on-chip oscillator on f <sub>OCO</sub> = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1			μA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1			μA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off, T <sub>opr</sub> = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0			μA
		Stop mode	XIN clock off, T <sub>opr</sub> = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0			μA

**Table 5.26 Serial Interface**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300	—	ns
$t_{w(CKH)}$	CLKi input "H" width	150	—	ns
$t_{w(CKL)}$	CLKi Input "L" width	150	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	70	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

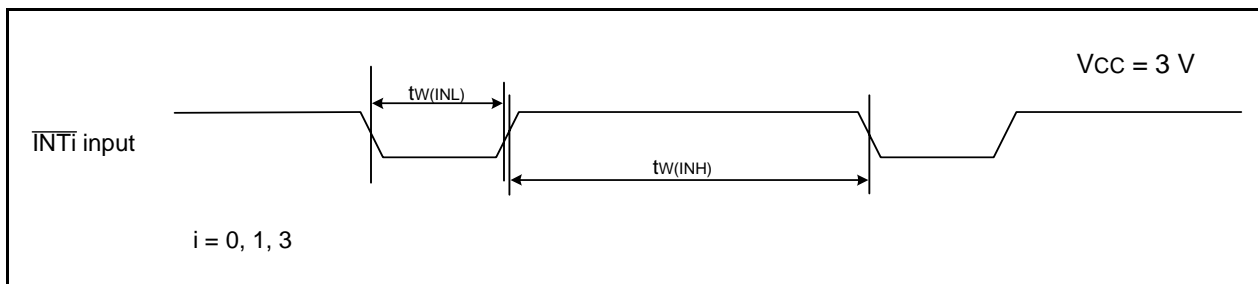
i = 0 or 1

**Figure 5.14 Serial Interface Timing Diagram when Vcc = 3 V****Table 5.27 External Interrupt  $\overline{INTi}$  (i = 0, 1, 3) Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input "H" width	380 <sup>(1)</sup>	—	ns
$t_{w(INL)}$	$\overline{INTi}$ input "L" width	380 <sup>(2)</sup>	—	ns

## NOTES:

1. When selecting the digital filter by the  $\overline{INTi}$  input filter select bit, use an  $\overline{INTi}$  input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the  $\overline{INTi}$  input filter select bit, use an  $\overline{INTi}$  input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

**Figure 5.15 External Interrupt  $\overline{INTi}$  Input Timing Diagram when Vcc = 3 V**

**Table 5.37 Flash Memory (Program ROM) Electrical Characteristics**

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance <sup>(2)</sup>	R8C/26 Group	100 <sup>(3)</sup>	–	–	times
		R8C/27 Group	1,000 <sup>(3)</sup>	–	–	times
–	Byte program time		–	50	400	μs
–	Block erase time		–	0.4	9	s
t <sub>d</sub> (SR-SUS)	Time delay from suspend request until suspend		–	–	97 + CPU clock × 6 cycles	μs
–	Interval from erase start/restart until following suspend request		650	–	–	μs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycles	μs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time <sup>(7)</sup>	Ambient temperature = 55°C	20	–	–	year

**NOTES:**

1. V<sub>CC</sub> = 2.7 to 5.5 V at T<sub>opr</sub> = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance  
The programming and erasure endurance is defined on a per-block basis.  
If the programming and erasure endurance is n (n = 100 or 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.  
However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

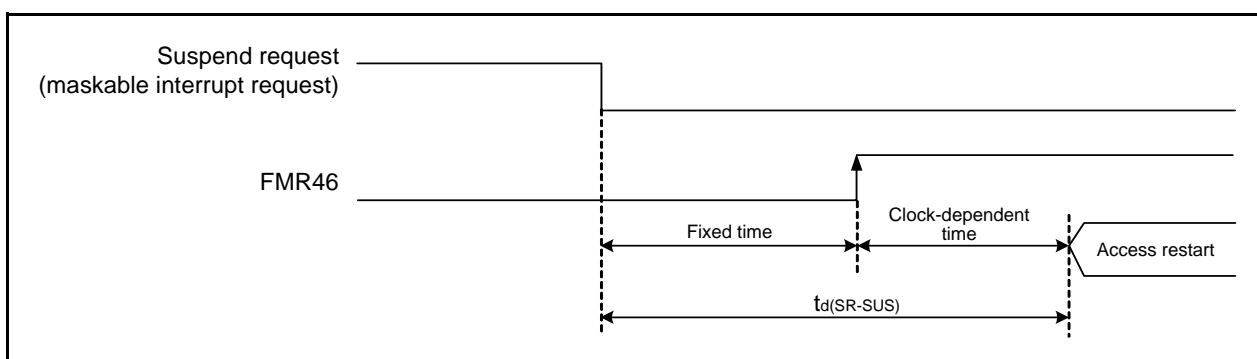


Figure 5.21 Time delay until Suspend

Table 5.39 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V <sub>det1</sub>	Voltage detection level <sup>(2, 4)</sup>		2.70	2.85	3.0	V
t <sub>d</sub> (V <sub>det1</sub> -A)	Voltage monitor 1 reset generation time <sup>(5)</sup>		—	40	200	μs
—	Voltage detection circuit self power consumption	VCA26 = 1, V <sub>CC</sub> = 5.0 V	—	0.6	—	μA
t <sub>d</sub> (E-A)	Waiting time until voltage detection circuit operation starts <sup>(3)</sup>		—	—	100	μs
V <sub>ccmin</sub>	MCU operating voltage minimum value		2.70	—	—	V

## NOTES:

- The measurement condition is V<sub>CC</sub> = 2.7 to 5.5 V and T<sub>opr</sub> = -40 to 85°C (J version) / -40 to 125°C (K version).
- Hold V<sub>det2</sub> > V<sub>det1</sub>.
- Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
- This parameter shows the voltage detection level when the power supply drops.  
The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.
- Time until the voltage monitor 1 reset is generated after the voltage passes V<sub>det1</sub> when V<sub>CC</sub> falls. When using the digital filter, its sampling time is added to t<sub>d</sub>(V<sub>det1</sub>-A). When using the voltage monitor 1 reset, maintain this time until V<sub>CC</sub> = 2.0 V after the voltage passes V<sub>det1</sub> when the power supply falls.

Table 5.40 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V <sub>det2</sub>	Voltage detection level <sup>(2)</sup>		3.3	3.6	3.9	V
t <sub>d</sub> (V <sub>det2</sub> -A)	Voltage monitor 2 reset/interrupt request generation time <sup>(3, 5)</sup>		—	40	200	μs
—	Voltage detection circuit self power consumption	VCA27 = 1, V <sub>CC</sub> = 5.0 V	—	0.6	—	μA
t <sub>d</sub> (E-A)	Waiting time until voltage detection circuit operation starts <sup>(4)</sup>		—	—	100	μs

## NOTES:

- The measurement condition is V<sub>CC</sub> = 2.7 to 5.5 V and T<sub>opr</sub> = -40 to 85°C (J version) / -40 to 125°C (K version).
- Hold V<sub>det2</sub> > V<sub>det1</sub>.
- Time until the voltage monitor 2 reset/interrupt request is generated after the voltage passes V<sub>det2</sub>.
- Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
- When using the digital filter, its sampling time is added to t<sub>d</sub>(V<sub>det2</sub>-A). When using the voltage monitor 2 reset, maintain this time until V<sub>CC</sub> = 2.0 V after the voltage passes V<sub>det2</sub> when the power supply falls.

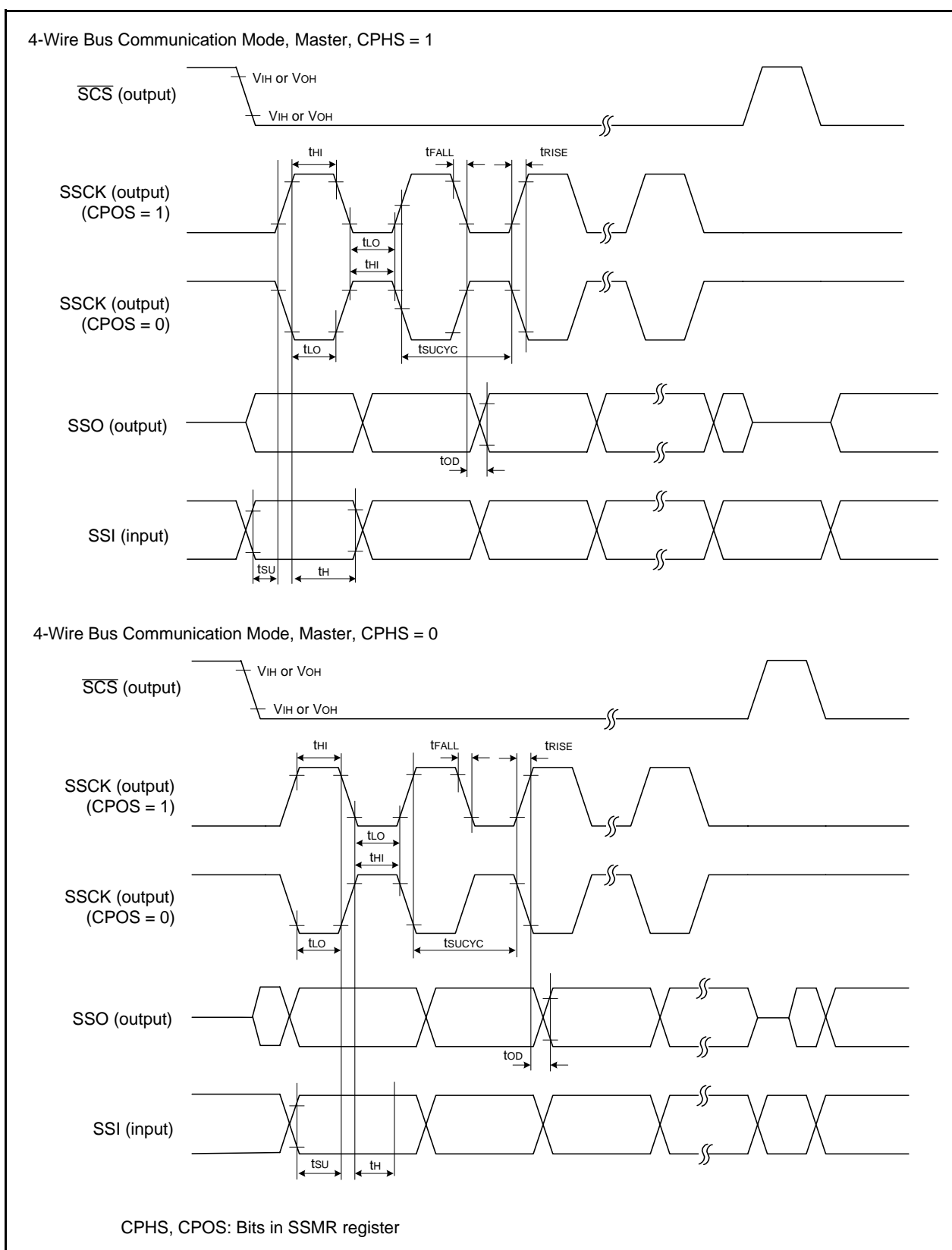
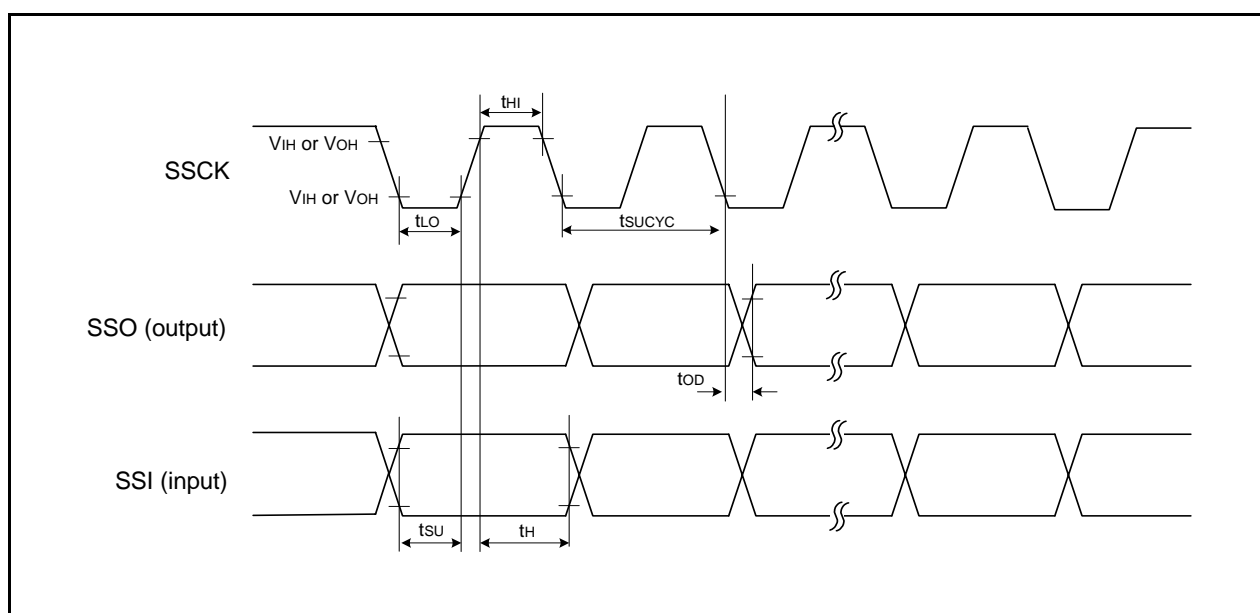


Figure 5.23 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)





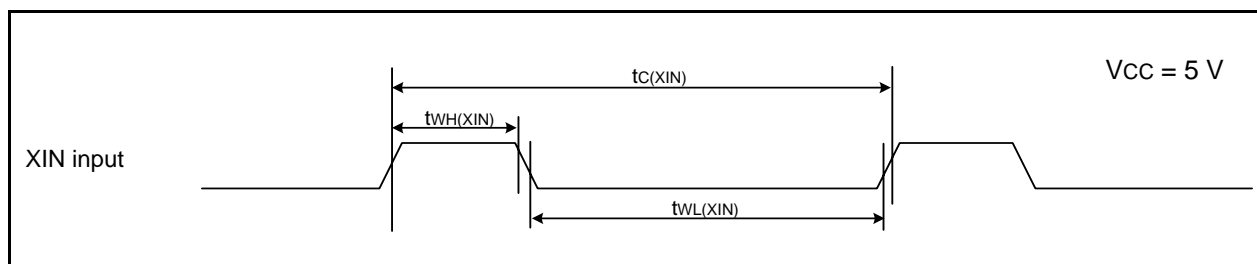
**Figure 5.25 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)**

**Table 5.48 Electrical Characteristics (2) [V<sub>CC</sub> = 5 V]**  
**(T<sub>opr</sub> = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.)**

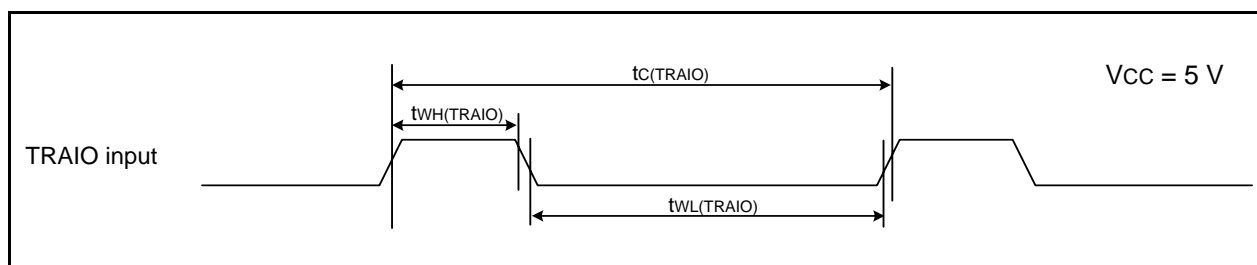
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
I <sub>CC</sub>	Power supply current (V <sub>CC</sub> = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are V <sub>SS</sub>	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz (J version) Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN clock off High-speed on-chip oscillator on fOCO = 20 MHz (J version) Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division			mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8			mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1			μA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1			μA
		Stop mode	XIN clock off, T <sub>opr</sub> = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0			μA
			XIN clock off, T <sub>opr</sub> = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0			μA
			XIN clock off, T <sub>opr</sub> = 125°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0			μA

**Timing Requirements****(Unless Otherwise Specified:  $V_{CC} = 5\text{ V}$ ,  $V_{SS} = 0\text{ V}$  at  $T_{opr} = 25^{\circ}\text{C}$ ) [ $V_{CC} = 5\text{ V}$ ]****Table 5.49 XIN Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input "H" width	25	–	ns
$t_{WL(XIN)}$	XIN input "L" width	25	–	ns

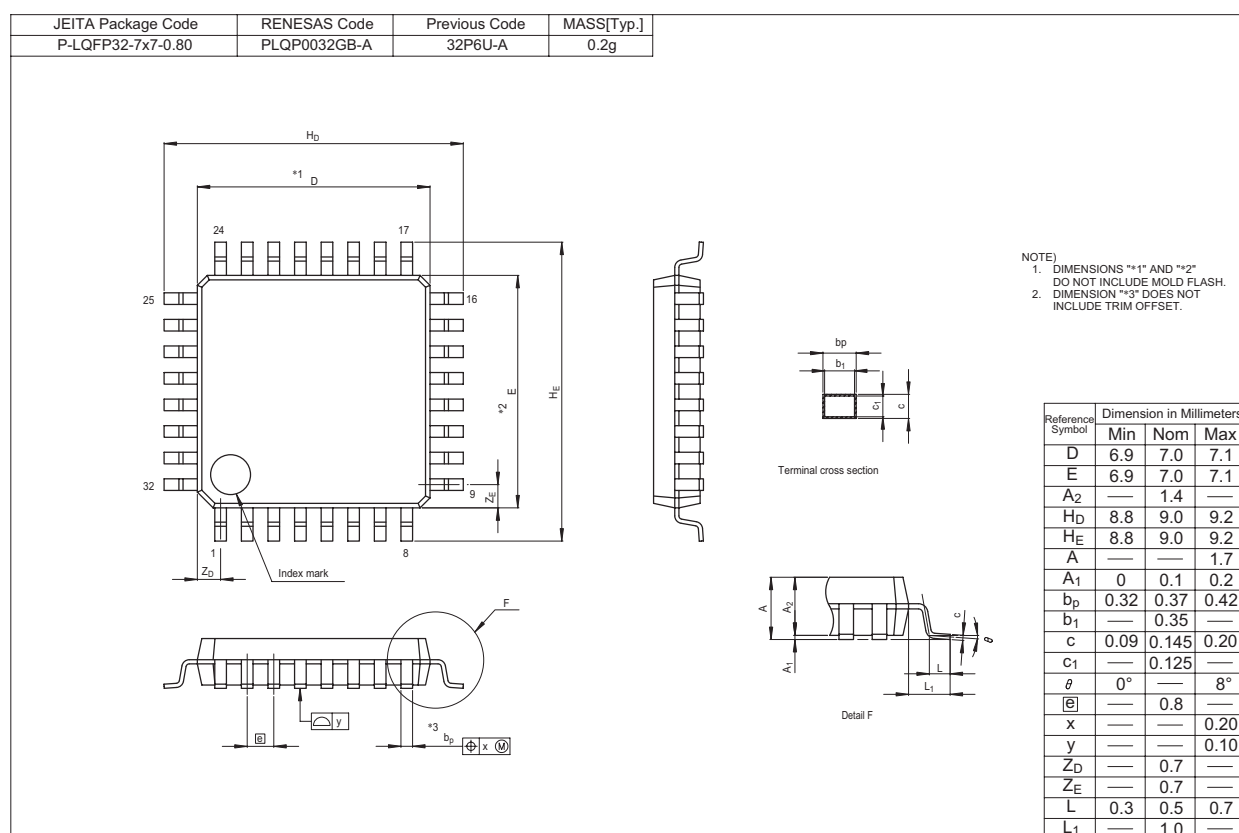
**Figure 5.27 XIN Input Timing Diagram when  $V_{CC} = 5\text{ V}$** **Table 5.50 TRAIO Input**

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input "H" width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input "L" width	40	–	ns

**Figure 5.28 TRAIO Input Timing Diagram when  $V_{CC} = 5\text{ V}$**

## Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Technology website.



# REVISION HISTORY

# R8C/26 Group, R8C/27 Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.30	May 25, 2007	16	Figure 3.2 part number revised
		30	Table 5.10 revised
		53	Table 5.39 NOTE4 added
		55	Table 5.42 revised
1.40a	Jun 14, 2007	5, 7	Table 1.3 and Table 1.4 revised
2.00	Mar 01, 2008	1, 49	1.1, 5.2 "J and K versions are ..." deleted
		5, 7	Table 1.3, Table 1.4 revised
		11	Table 1.6 NOTE3 added
		15, 16	Figure 3.1, Figure 3.2; "Expanded area" deleted
		17	Table 4.1 "002Ch" added
		18	Table 4.2 "0036h"; J, K version "0100X000b" → "0100X001b"
		24, 49	Table 5.2, Table 5.35; NOTE2 revised
2.10	Sep 26, 2008	30	Table 5.10 revised, NOTE4 added
		–	"RENESAS TECHNICAL UP DATE" reflected: TN-16C-A172A/E
		26, 51	Table 5.4, Table 5.37 NOTE2, NOTE4 revised
		27, 52	Table 5.5, Table 5.38 NOTE2, NOTE5 revised
		53	Table 5.39 Parameter: Voltage monitor 1 reset generation time added NOTE5 added
			Table 5.40 revised
		54	Table 5.41 revised
			Figure 5.22 revised

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